

XN01601 (XN1601)

Silicon PNP epitaxial planar type (Tr1)
Silicon NPN epitaxial planar type (Tr2)

For general amplification

■ Features

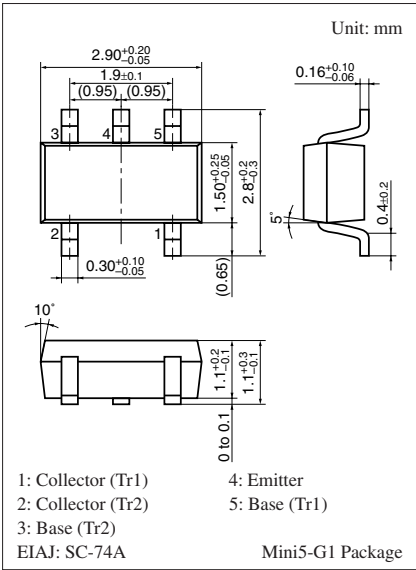
- Two elements incorporated into one package (Emitter-coupled transistors)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- 2SB0709A (2SB709A) + 2SD0601A (2SD601A)

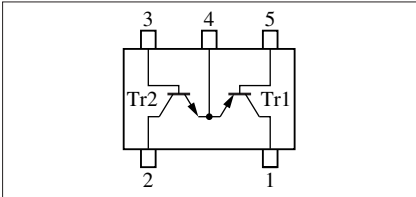
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V_{CBO}	-60	V
	Collector-emitter voltage (Base open)	V_{CEO}	-50	V
	Emitter-base voltage (Collector open)	V_{EBO}	-7	V
	Collector current	I_C	-100	mA
	Peak collector current	I_{CP}	-200	mA
Tr2	Collector-base voltage (Emitter open)	V_{CBO}	60	V
	Collector-emitter voltage (Base open)	V_{CEO}	50	V
	Emitter-base voltage (Collector open)	V_{EBO}	7	V
	Collector current	I_C	100	mA
	Peak collector current	I_{CP}	200	mA
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 7S

Internal Connection



Note) The part number in the parenthesis shows conventional part number.

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10\ \mu\text{A}$, $I_E = 0$	-60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2\ \text{mA}$, $I_B = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10\ \mu\text{A}$, $I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20\ \text{V}$, $I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -10\ \text{V}$, $I_B = 0$			-100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10\ \text{V}$, $I_C = -2\ \text{mA}$	160		460	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\ \text{mA}$, $I_B = -10\ \text{mA}$		-0.3	-0.5	V
Transition frequency	f_T	$V_{CB} = -10\ \text{V}$, $I_E = 1\ \text{mA}$, $f = 200\ \text{MHz}$		80		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$		2.7		pF

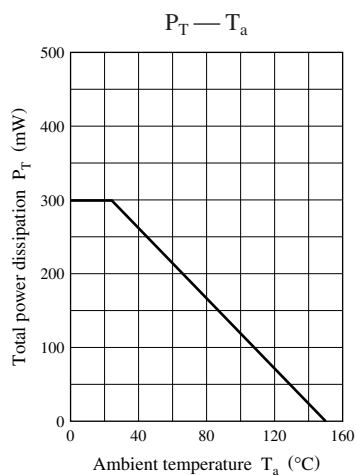
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

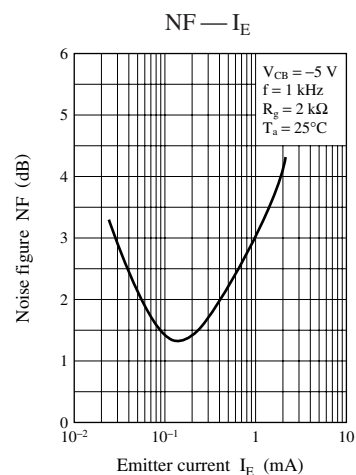
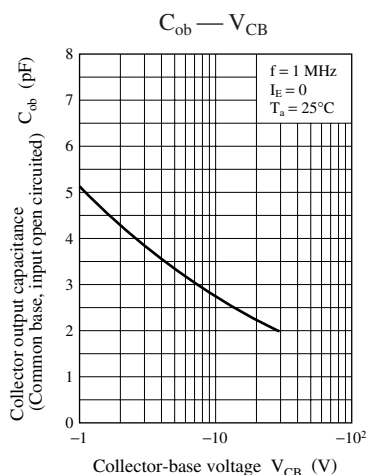
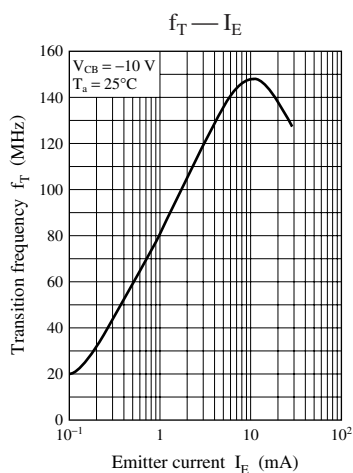
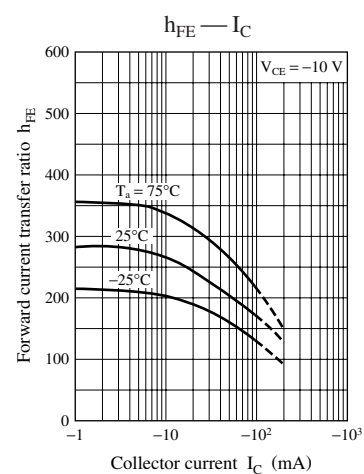
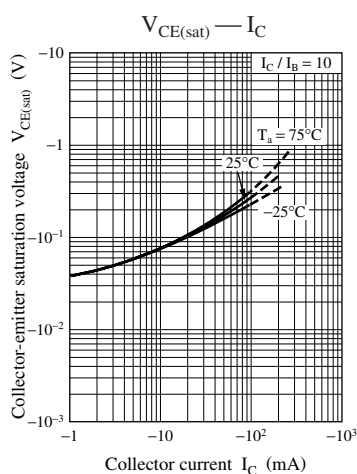
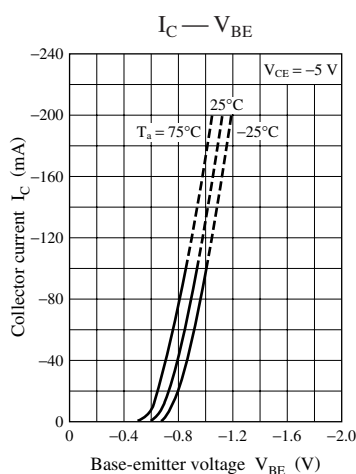
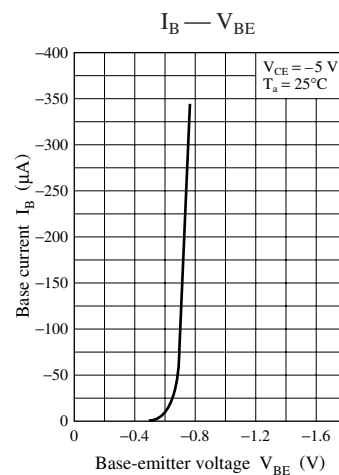
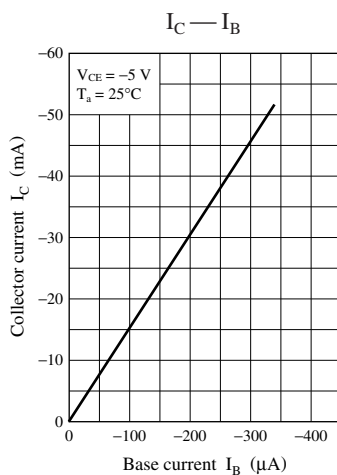
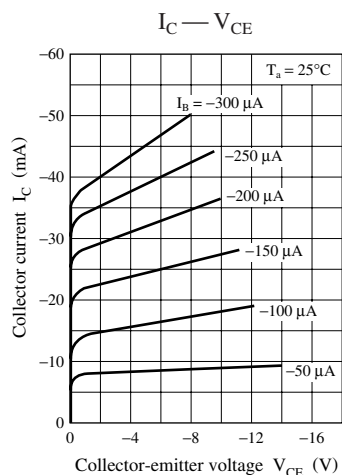
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10\ \mu\text{A}$, $I_E = 0$	60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2\ \text{mA}$, $I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10\ \mu\text{A}$, $I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20\ \text{V}$, $I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10\ \text{V}$, $I_B = 0$			100	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10\ \text{V}$, $I_C = 2\ \text{mA}$	160		460	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\ \text{mA}$, $I_B = 10\ \text{mA}$		0.1	0.3	V
Transition frequency	f_T	$V_{CB} = 10\ \text{V}$, $I_E = -2\ \text{mA}$, $f = 200\ \text{MHz}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$		3.5		pF

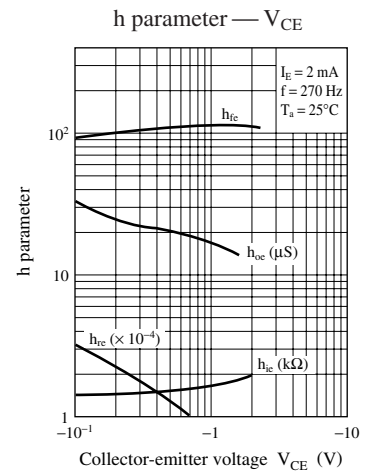
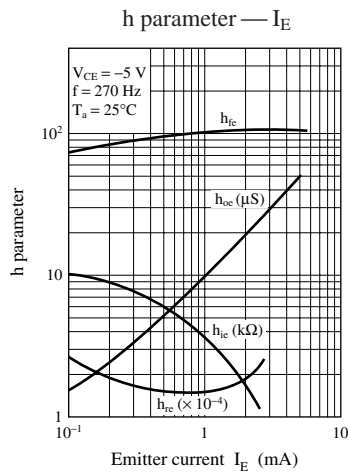
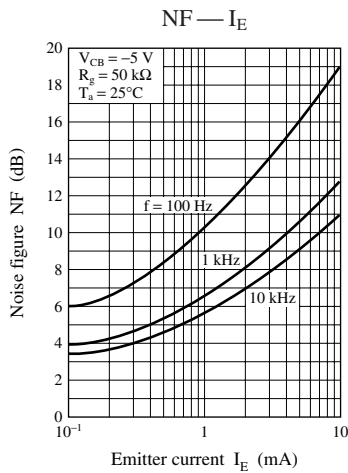
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Common characteristics chart

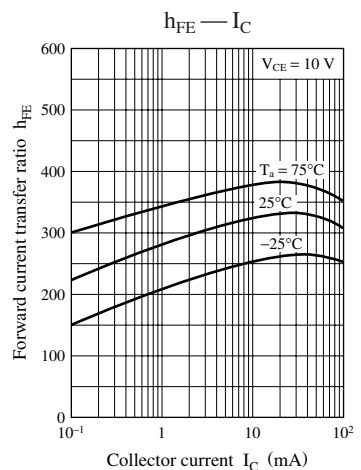
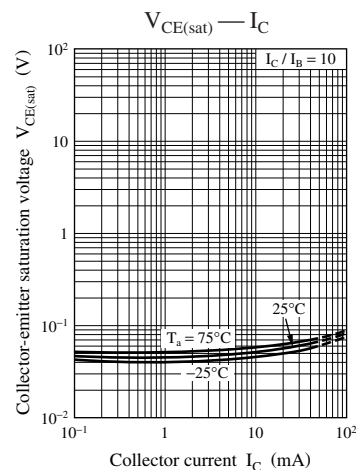
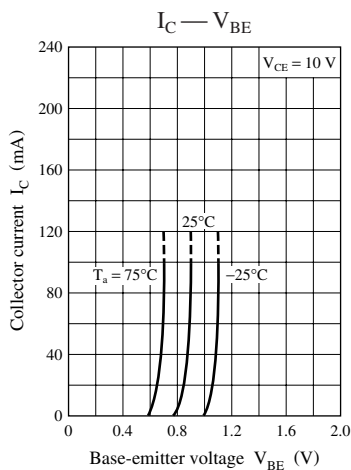
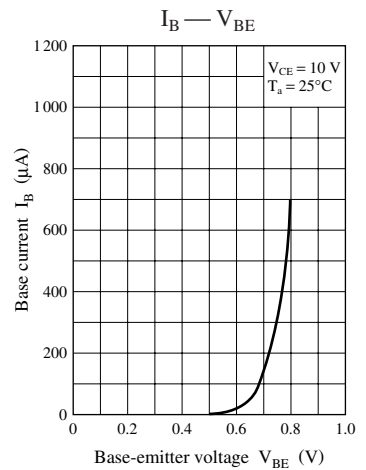
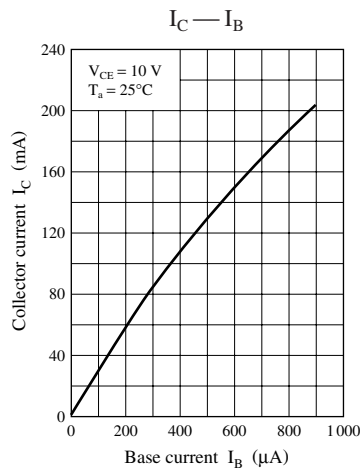
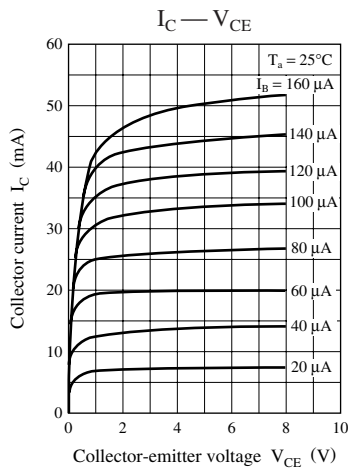


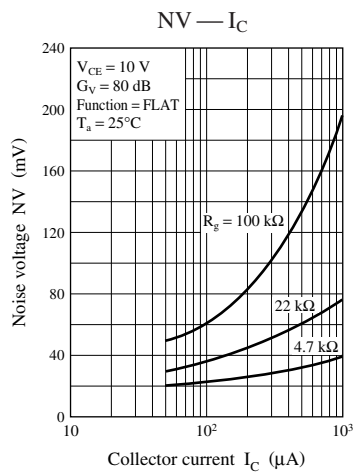
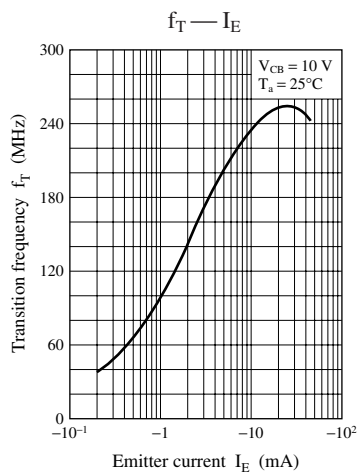
Characteristics charts of Tr1





Characteristics charts of Tr2





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